

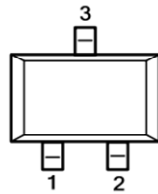
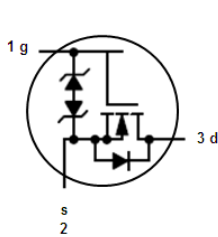
N-Channel 60V MOSFET

Features:

- Low on-resistance.
- Fast switching speed.
- Low voltage drive.
- Halogen free
- ESD protected 2000V

Application

- DC-DC
- Portable appliance
- Power management



Top View
SOT23S-3L

$B_{VDSS} = 60V$,
 $R_{DS(ON)} < 2.3\Omega @ V_{GS} = 10V$
 $R_{DS(ON)} < 2.7\Omega @ V_{GS} = 5V$
 $I_D = 380mA$

Absolute Maximum Ratings ($T_A = 25^\circ C$ Unless Otherwise Noted)

Parameter	Symbol	2N7002K	Unit
	Marking	RK	
Drain-Source Voltage	V_{DSS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current (Note 1)	I_D	$T_A = 25^\circ C$	380
		$T_A = 85^\circ C$	270
Pulsed Drain Current ($t_p = 10 \mu s$)	I_{DM}	1.5	A
Power Dissipation (Note 1)	P_D	420	mW
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	300	$^\circ C/W$
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to 150	$^\circ C$

Note : 1. Surface mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces)

N-Channel 60V MOSFET
Electrical Characteristics ($T_A = 25^\circ\text{C}$ Unless Otherwise Specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
Static						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	60	--	--	V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	1	--	2.5	V
I_{GSS}	Gate-Body Leakage	$V_{DS}=0V, V_{GS}=\pm 20V$	--	--	± 10	μA
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=60V, V_{GS}=0V$	--	--	1	μA
$R_{DS(on)}$	Drain-Source On-Resistance	$V_{GS}=10V, I_D=0.5A$	--	1.4	2.3	Ω
		$V_{GS}=5V, I_D=0.05A$	--	1.7	2.7	Ω
V_{SD}	Diode Forward Voltage (Note 2)	$I_S = 115mA, V_{GS} = 0V$	--	--	1.2	V
g_{FS}	Forward Transconductance	$I_D=0.2A, V_{SD}=5V$	80	--	--	mS
Dynamic						
C_{iss}	Input Capacitance	$V_{DS}=25V, V_{GS}=0V, f=1MHz$	--	25	50	pF
C_{oss}	Output Capacitance		--	5.5	25	
C_{rss}	Reverse Transfer Capacitance		--	3	5	
Q_g	Total Gate Charge	$V_{DS} = 10V, V_{GS} = 4.5V,$ $I_D = 0.5A$	--	0.71	--	nC
Q_{GS}	Gate-to-Source Charge		--	0.6	--	
Q_{GD}	Gate-to-Drain Charge		--	0.16	--	
$t_{d(on)}$	Turn-On Delay Time (Note 3)	$V_{DS} = 10V, I_D = 0.5A,$ $V_{EN} = 10V, R_G = 25\Omega$	--	1.5	10	ns
t_r	Turn-On Rise Time		--	22	10	
$t_{d(off)}$	Turn-Off Delay Time		--	3	40	
t_f	Turn-On Fall Time		--	22	30	

Note : 2. Pulse Test: pulse width $\leq 300 \mu s$, duty cycle $\leq 2\%$

3. Switching characteristics are independent of operating junction temperatures

N-Channel 60V MOSFET

TYPICAL ELECTRICAL CHARACTERISTICS

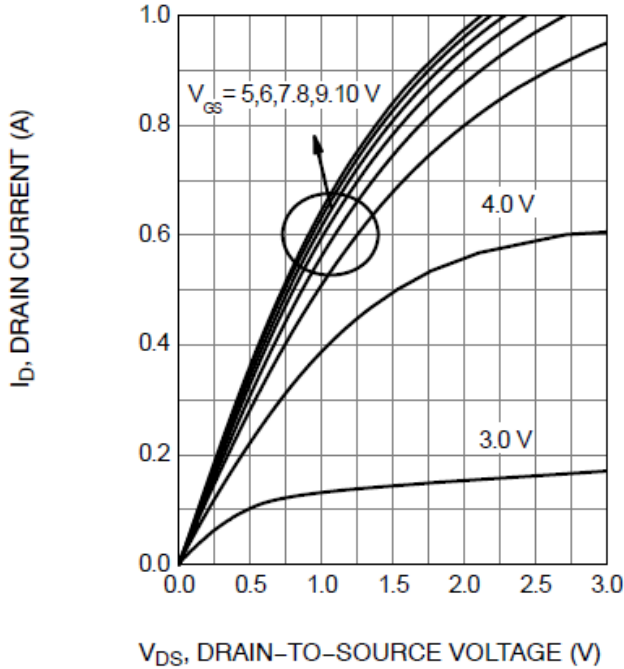


Figure 1. On-Region Characteristics

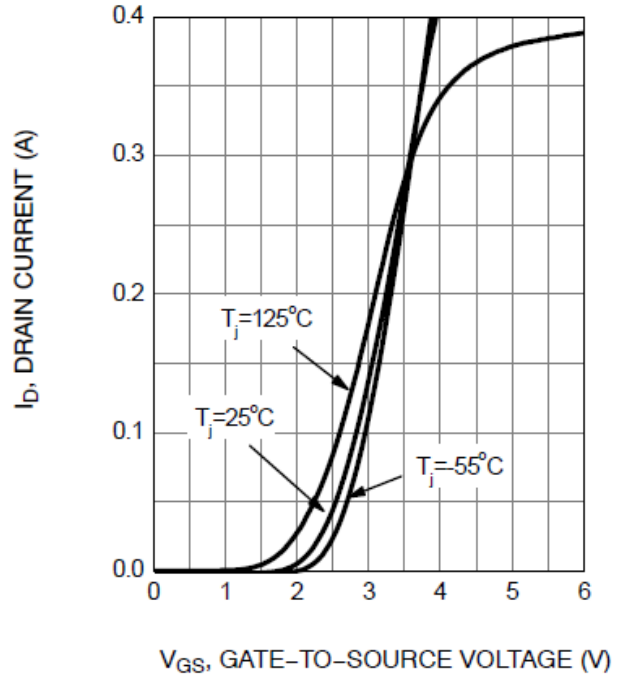


Figure 2. Transfer Characteristics

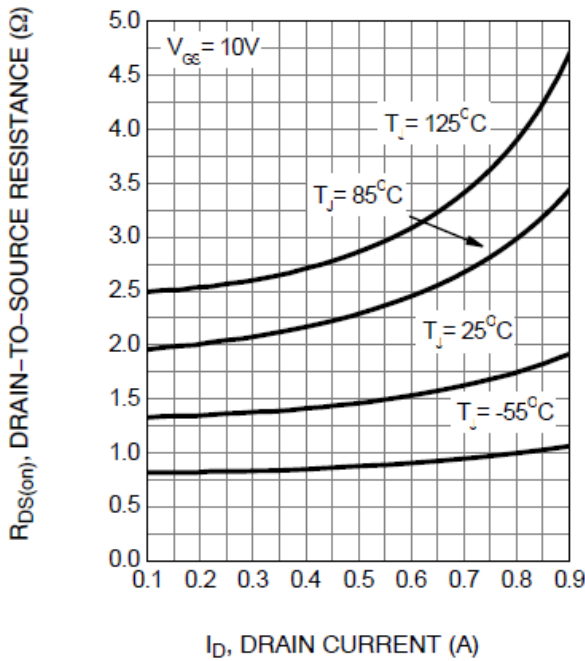


Figure 3. On-Resistance vs. Drain Current and Temperature

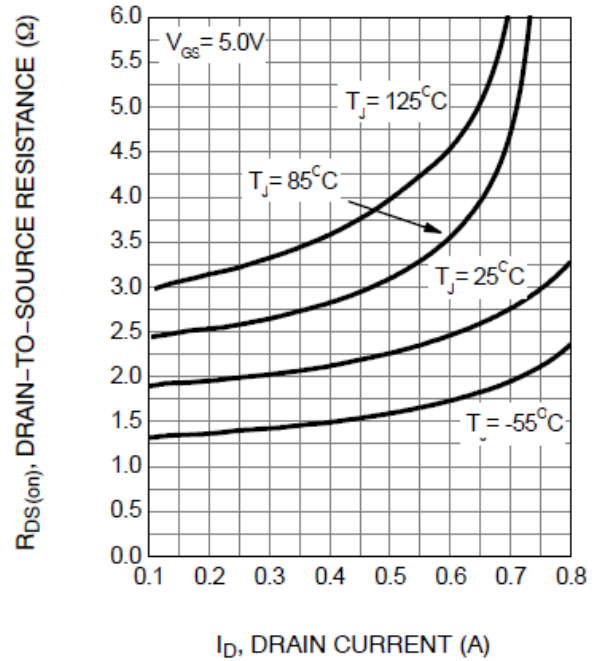


Figure 4. On-Resistance vs. Drain Current and Temperature

N-Channel 60V MOSFET

TYPICAL ELECTRICAL CHARACTERISTICS

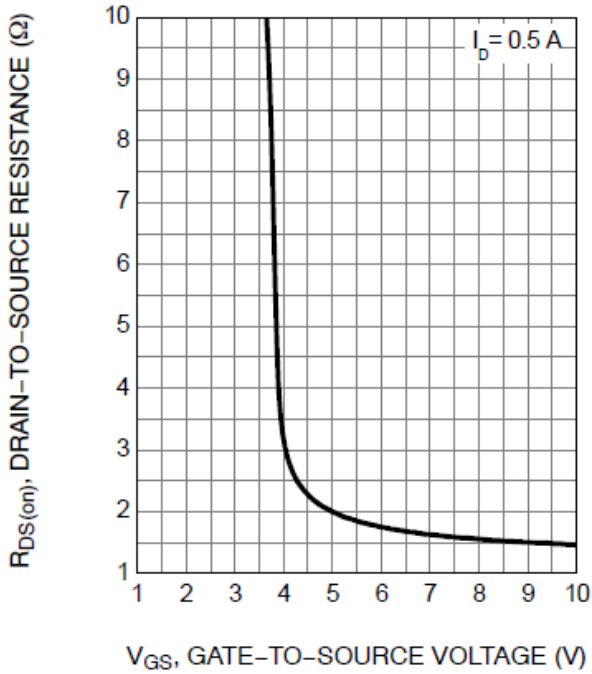


Figure 5. On-Resistance vs. Gate-to-Source Voltage

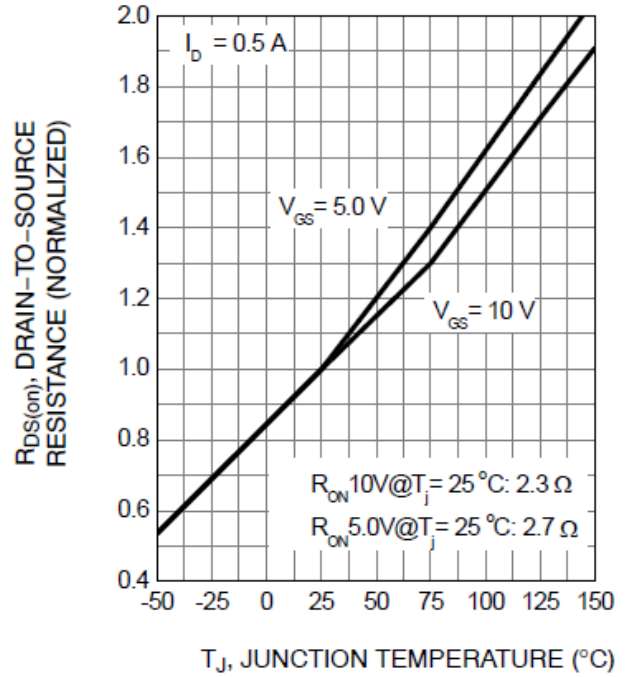


Figure 6. On-Resistance Variation with Temperature

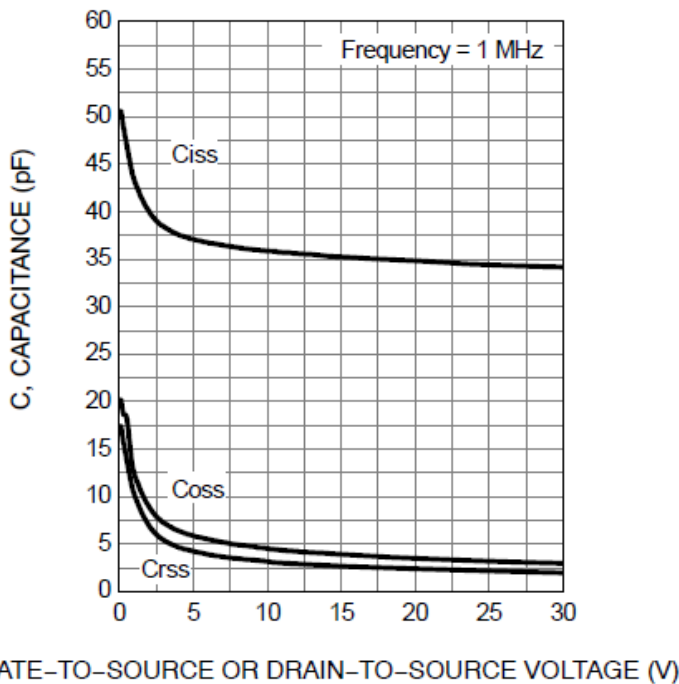


Figure 7. Capacitance Variation

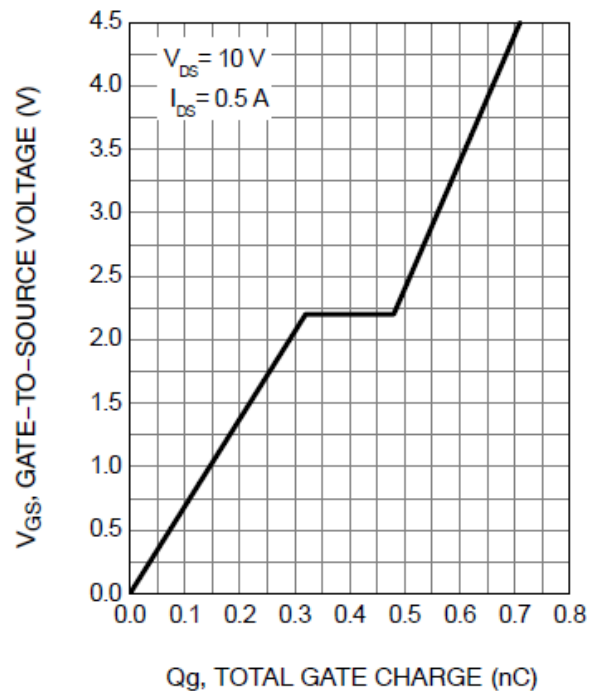


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

N-Channel 60V MOSFET

TYPICAL ELECTRICAL CHARACTERISTICS

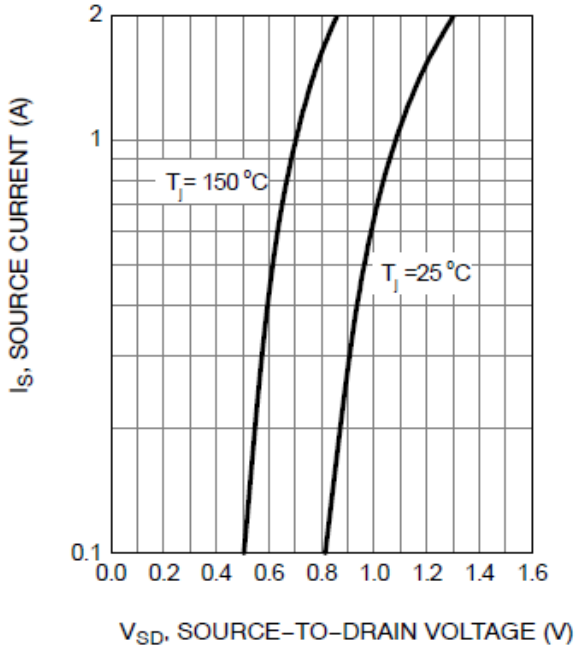


Figure 9. Diode Forward Voltage vs. Current

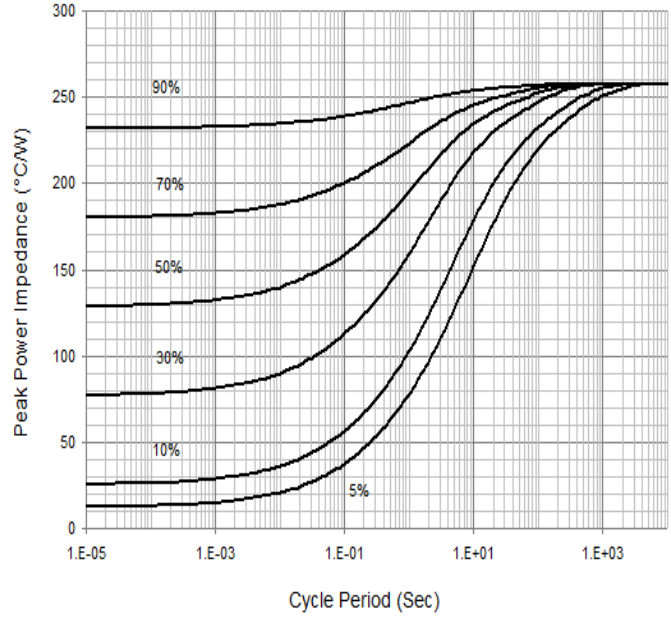


Figure 10. Thermal Transient Impedance

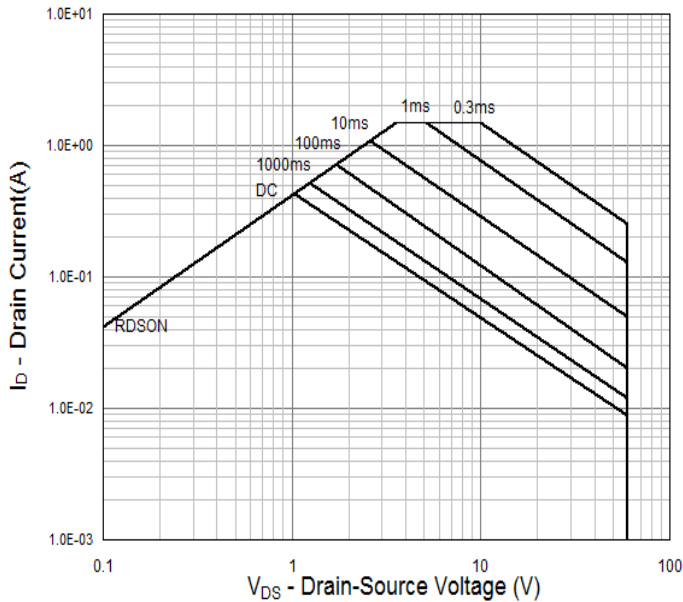
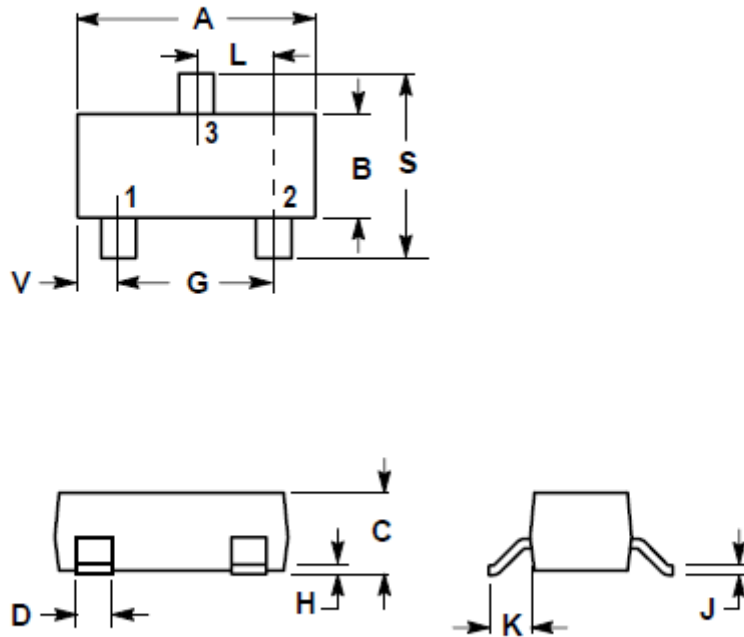


Figure 11. Safe Operation Area

N-Channel 60V MOSFET

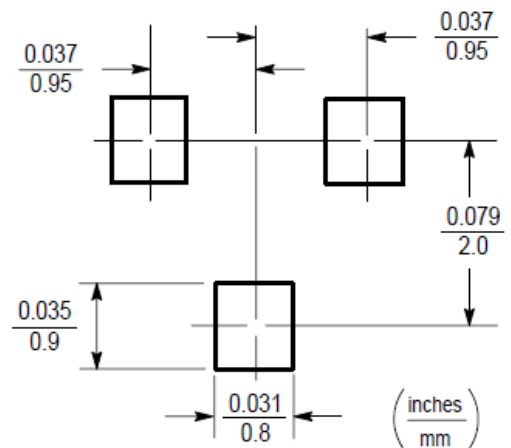
Package Dimension : SOT-23



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M,1982
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
H	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60



Important Notice and Disclaimer

LSC reserves the right to make changes to this document and its products and specifications at any time without notice. Customers should obtain and confirm the latest product information and specifications before final design, purchase or use.

LSC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does LSC assume any liability for application assistance or customer product design. LSC does not warrant or accept any liability with products which are purchased or used for any unintended or unauthorized application.

No license is granted by implication or otherwise under any intellectual property rights of LSC.

LSC products are not authorized for use as critical components in life support devices or systems without express written approval of LSC.